

**isc Silicon NPN Power Transistors**
**D44VH10**
**DESCRIPTION**

- Low Collector-Emitter Saturation Voltage  
:  $V_{CE(sat)} = 0.4V(\text{Max}) @ I_C = 8A$
- Fast Switching Speeds
- Complement to Type D45VH10
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

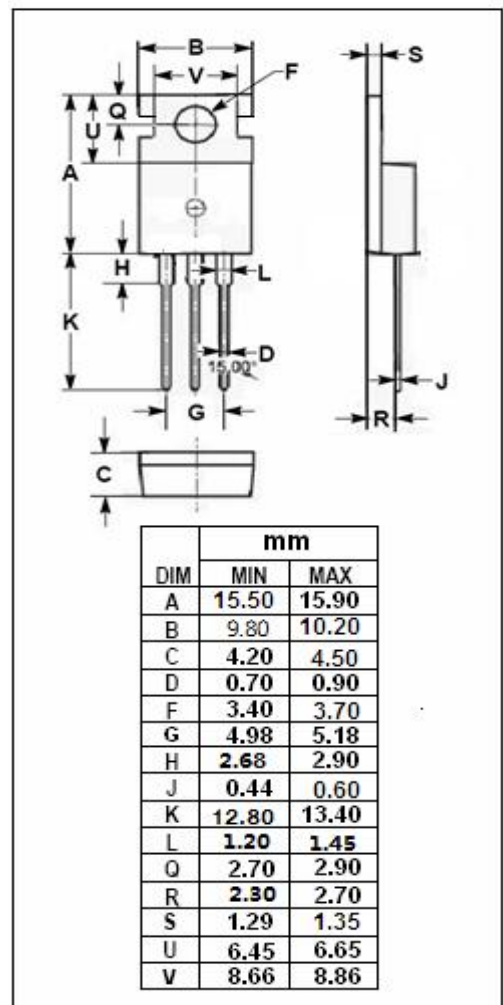
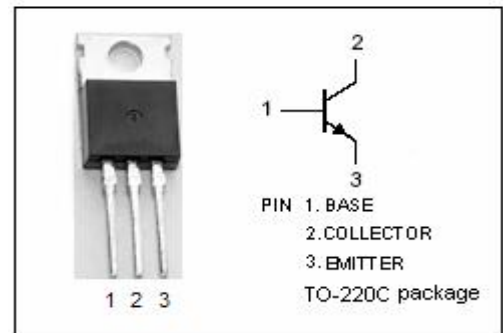
- Designed for general purpose power amplification and switching such as output or driver stages in applications such as switching regulators, converters and power amplifier.

**ABSOLUTE MAXIMUM RATINGS ( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{CBO}$	Collector-Base Voltage	100	V
$V_{EBO}$	Emitter-Base Voltage	7.0	V
$I_C$	Collector Current-Continuous	15	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	83	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

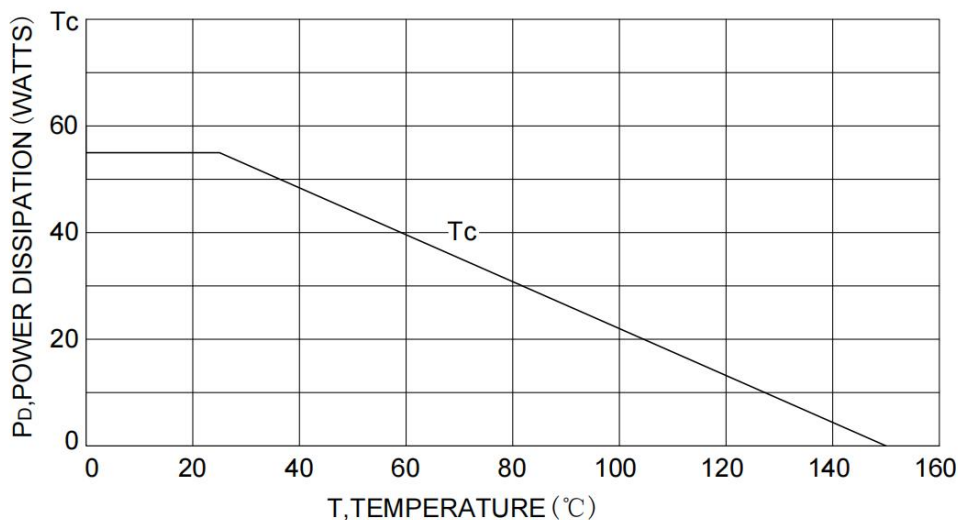
SYMBOL	PARAMETER	MAX	UNIT
$R_{th(j-c)}$	Thermal Resistance, Junction to Case	1.5	$^\circ\text{C/W}$



**isc Silicon NPN Power Transistors**
**D44VH10**
**ELECTRICAL CHARACTERISTICS**

 T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7	-	V
V <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA; I <sub>B</sub> = 0	80	-	V
V <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> =1mA; I <sub>B</sub> = 0	100	-	V
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0	-	10	μ A
I <sub>CEO</sub>	Collector-Emitter Cutoff Current	V <sub>CE</sub> = 80V; I <sub>B</sub> = 0	-	1	mA
I <sub>CBO</sub>	Collector-Emitter Cutoff Current	V <sub>CE</sub> = 80V; I <sub>E</sub> = 0	-	100	μ A
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 0.4 A	-	0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 8A ;I <sub>B</sub> = 0.4 A	-	1.2	V
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 2A ; V <sub>CE</sub> = 1V	35	-	-
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A ; V <sub>CE</sub> = 1V	20	-	-

**• Power and temperature curve**


---

**isc Silicon NPN Power Transistors****D44VH10**

---

**NOTICE:**

ISC reserves the rights to make changes of the content herein the datasheet at any time without notification. The information contained herein is presented only as a guide for the applications of our products.

ISC products are intended for usage in general electronic equipment. The products are not designed for use in equipment which require specialized quality and/or reliability, or in equipment which could have applications in hazardous environments, aerospace industry, or medical field. Please contact us if you intend our products to be used in these special applications.

ISC makes no warranty or guarantee regarding the suitability of its products for any particular purpose, nor does ISC assume any liability arising from the application or use of any products, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

